TRANSFER-MOLD TYPE INSULATED TYPE

#### PS21869



#### INTEGRATED POWER FUNCTIONS

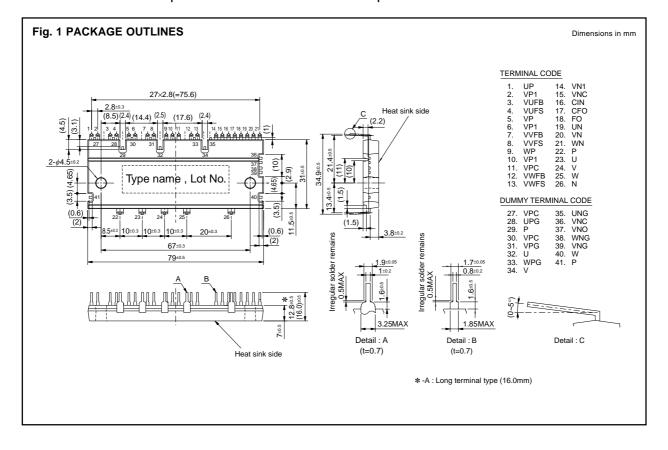
 $600\mbox{V}/50\mbox{A}$  low-loss CSTBT inverter bridge for 3 phase DC-to-AC power conversion

#### INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

- For upper-leg IGBTs: Drive circuit, High voltage isolated high-speed level shifting, Control supply under-voltage (UV) protection.
- For lower-leg IGBTs: Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC). (Fig.3)
- Fault signaling: Corresponding to an SC fault (Lower-side IGBT) or a UV fault (Lower-side supply).
- Input interface: 5V line CMOS/TTL compatible. (High Active)
- UL Approved : Yellow Card No. E80276

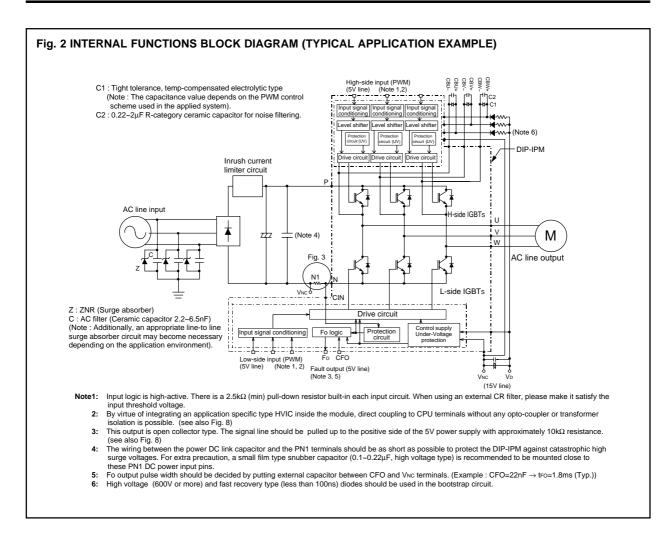
### **APPLICATION**

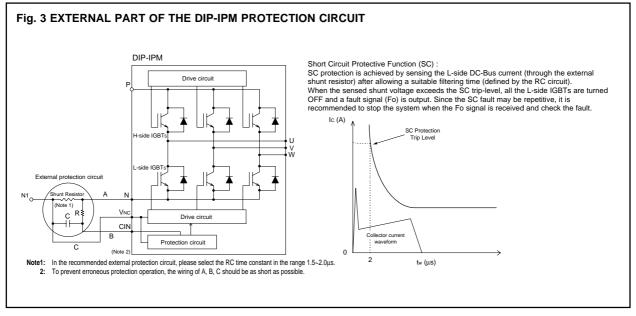
AC100V~200V three-phase inverter drive for small power motor control.





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# **MAXIMUM RATINGS** ( $T_j = 25^{\circ}C$ , unless otherwise noted)

#### **INVERTER PART**

Symbol	Parameter	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P-N	450	V
VCC(surge)	Supply voltage (surge)	Applied between P-N	500	V
VCES	Collector-emitter voltage		600	V
±lc	Each IGBT collector current	Tf = 25°C	50	Α
±ICP	Each IGBT collector current (peak)	Tf = 25°C, less than 1ms	100	Α
Pc	Collector dissipation	Tf = 25°C, per 1 chip	70.4	W
Tj	Junction temperature	(Note 1)	-20~+125	°C

Note 1 : The maximum junction temperature rating of the power chips integrated within the DIP-IPM is  $150^{\circ}$ C (@ Tf  $\leq 100^{\circ}$ C) however, to ensure safe operation of the DIP-IPM, the average junction temperature should be limited to Tj(ave)  $\leq 125^{\circ}$ C (@ Tf  $\leq 100^{\circ}$ C).

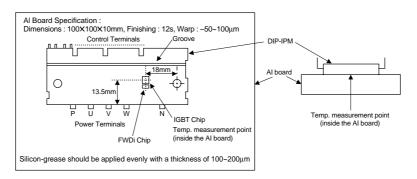
## **CONTROL (PROTECTION) PART**

Symbol	Parameter	Condition	Ratings	Unit
VD	Control supply voltage	Applied between VP1-VPC, VN1-VNC	20	V
VDB	Control supply voltage	Applied between VUFB-VUFS, VVFB-VVFS, VWFB-VWFS	20	V
VIN	Input voltage	Applied between UP, VP, WP-VPC, UN, VN, WN-VNC	-0.5~VD+0.5	V
VFO	Fault output supply voltage	Applied between Fo-VNC	-0.5~VD+0.5	V
IFO	Fault output current	Sink current at Fo terminal	1	mA
Vsc	Current sensing input voltage	Applied between CIN-VNC	-0.5~VD+0.5	V

#### **TOTAL SYSTEM**

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Self protection supply voltage limit (short circuit protection capability)	$VD = 13.5 \sim 16.5 \text{V}$ , Inverter part $T_j = 125 ^{\circ}\text{C}$ , non-repetitive, less than 2 μs	400	V
Tf	Module case operation temperature	(Note 2)	-20~+100	°C
Tstg	Storage temperature		-40~+125	°C
Viso	Isolation voltage	60Hz, Sinusoidal, AC 1 minute, connection pins to heat-sink plate	2500	Vrms

#### Note 2: Tf MEASUREMENT POINT





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#### THERMAL RESISTANCE

Symbol Parameter	Davamatar	Condition	Limits			l lmit
	Condition		Тур.	Max.	Unit	
Rth(j-f)Q	Junction to case thermal	Inverter IGBT part (per 1/6 module)	_	_	1.42	°C/W
Rth(j-f)F	resistance (Note 3)	Inverter FWDi part (per 1/6 module)	_	_	2.00	°C/W

 $\textbf{Note 3:} \ \ \text{Grease with good thermal conductivity should be applied evenly with about +100} \\ \mu\text{m} \sim +200 \\ \mu\text{m on the contacting surface of DIP-IPM}$ and heat-sink.

# **ELECTRICAL CHARACTERISTICS** (Tj = 25°C, unless otherwise noted)

#### **INVERTER PART**

Cumple of	D-m-m-at-m	Condition		Limits			Unit	
Symbol	Symbol Parameter		Condition		Тур.	Max.	Unit	
VCE(cot)	Collector-emitter saturation	VD = VDB = 15V	Ic = 50A, Tj = 25°C	_	1.50	2.00	`,,	
VCE(sat) voltage	VIN = 5V	Ic = 50A, Tj = 125°C	_	1.60	2.10	V		
VEC	FWDi forward voltage	Tj = 25°C, -IC = 50A, VIN = 0V		_	1.70	2.20	V	
ton		Vcc = 300V, VD = VDB = 15V		0.70	1.30	1.90	μs	
trr				_	0.30	_	μs	
tc(on)	Switching times	IC = 50A, Tj = 125°C, VIN	IC = 50A, T <sub>j</sub> = 125°C, VIN = $0 \leftrightarrow 5V$		0.40	0.60	μs	
toff		Inductive load (upper-lov	ver arm)	_	2.00	2.60	μs	
tc(off)				_	0.65	0.90	μs	
ICES	Collector-emitter cut-off		Tj = 25°C	_	_	1	mA	
	current	VCE = VCES	Tj = 125°C	_	_	10	IIIA	

#### **CONTROL (PROTECTION) PART**

Cumbal	Parameter		Condition			Limits		
Symbol	Parameter		Condition		Min.	Тур.	Max.	Unit
		VD = VDB = 15V Total of		of VP1-VPC, VN1-VNC	_	_	5.00	mA
lD	Circuit current	VIN = 5V	Vufb-	VUFS, VVFB-VVFS, VWFB-VWFS	_	_	0.40	mA
ם ו	Circuit current	VD = VDB = 15V	Total o	of VP1-VPC, VN1-VNC	_	_	7.00	mA
		VIN = 0V	VUFB-\	VUFS, VVFB-VVFS, VWFB-VWFS	_	_	0.55	mA
VFOH	Fault output voltage	Vsc = 0V, Fo circuit pull-up to 5V with $10k\Omega$			4.9	_	_	V
VFOL	Tault output voltage	VSC = 1V, IFO = 1mA			_	_	0.95	V
VSC(ref)	Short circuit trip level	$T_j = 25^{\circ}C, VD = 15V$ (Note 4)		0.43	0.48	0.53	V	
lin	Input current	VIN = 5V	VIN = 5V		1.0	1.5	2.0	mA
UVDBt				Trip level	10.0	_	12.0	V
UVDBr	Supply circuit under-voltage	T <sub>i</sub> ≤ 125°C		Reset level	10.5	_	12.5	V
UVDt	protection	1j≤125 C		Trip level	10.3	_	12.5	V
UVDr				Reset level	10.8	_	13.0	V
tFO	Fault output pulse width	CFO = 22nF (Note 5)		1.0	1.8	_	ms	
Vth(on)	ON threshold voltage	Applied between LID V/D W/D V/DO LINE V/N W/N V/NO		2.1	2.3	2.6	V	
Vth(off)	OFF threshold voltage	Applied between UP, VP, WP-VPC, UN, VN, WN-VNC			0.8 1.4	2.1	V	

Note 4: Short circuit protection is functioning only at the low-arms. Please select the value of the external shunt resistor such that the SC trip-



level is less than 85 A.

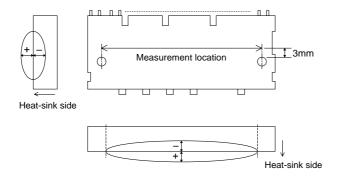
5: Fault signal is output when the low-arms short circuit or control supply under-voltage protective functions operate. The fault output pulsewidth tFo depends on the capacitance value of CFo according to the following approximate equation: CFo = 12.2 X 10<sup>-6</sup> X tFo [F].

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#### **MECHANICAL CHARACTERISTICS AND RATINGS**

Developmentary	Condition		Limits			l locia
Parameter		Min.	Тур.	Max.	Unit	
Mounting torque	Mounting screw : M4	Recommended 1.18 N·m	0.98	_	1.47	N⋅m
Weight			_	65	_	g
Heat-sink flatness		(Note 6)	-50	_	100	μm

#### Note 6: Measurement point of heat-sink flatness



#### **RECOMMENDED OPERATION CONDITIONS**

0	Downstein One Hitter		Limits			I I alt
Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
Vcc	Supply voltage	Applied between P-N	0	300	400	V
VD	Control supply voltage	Applied between VP1-VPC, VN1-VNC	13.5	15.0	16.5	V
VDB	Control supply voltage	Applied between VUFB-VUFS, VVFB-VVFS, VWFB-VWFS	13.0	15.0	18.5	V
$\Delta V$ D, $\Delta V$ DB	Control supply variation			_	1	V/μs
tdead	Arm shoot-through blocking time	For each input signal, Tf ≤ 100°C		_	_	μs
fPWM	PWM input frequency	$T_f \le 100^{\circ}C$ , $T_j \le 125^{\circ}C$		5	_	kHz
		Vcc = 300V, VD = 15V, fc = 5kHz				
lo	Allowable r.m.s. current	P.F = 0.8, sinusoidal	_	_	23	Arms
		$T_j \le 125^{\circ}C$ , $T_f \le 100^{\circ}C$ (Note 7)				
PWIN	Minimum input pulse width	ON (Note 8)	300	_	_	ns
VNC	VNC variation	between VNC-N (including surge)	-5.0	_	5.0	V

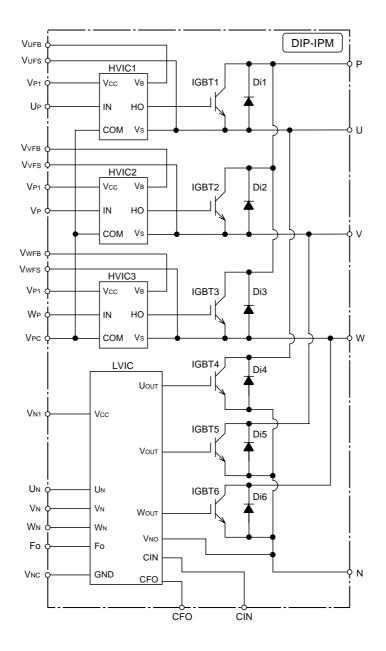
Note 7: The allowable r.m.s. current value depends on the actual application conditions.

8: The input pulse width less than PWIN might make no response.



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Fig. 4 THE DIP-IPM INTERNAL CIRCUIT





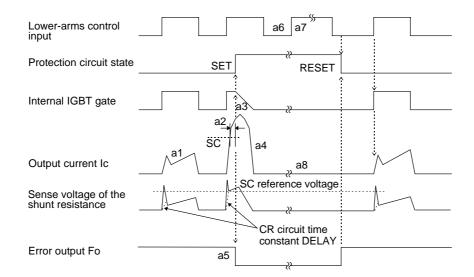
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## Fig. 5 TIMING CHARTS OF THE DIP-IPM PROTECTIVE FUNCTIONS

# [A] Short-Circuit Protection (Lower-arms only)

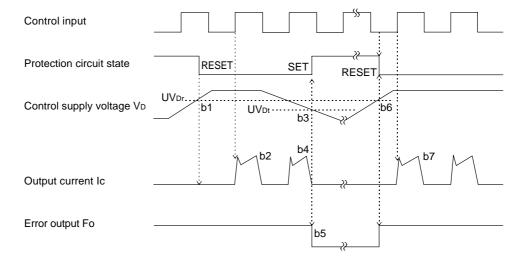
(With the external shunt resistance and CR connection)

- a1. Normal operation: IGBT ON and carrying current.
- a2. Short circuit current detection (SC trigger).
- a3. Hard IGBT gate interrupt.
- a4. IGBT turns OFF.
- a5. Fo timer operation starts: The pulse width of the Fo signal is set by the external capacitor CFo.
- a6. Input "L": IGBT OFF state.
- a7. Input "H": IGBT ON state, but during the Fo active signal period the IGBT doesn't turn ON.
- a8. IGBT OFF state.



#### [B] Under-Voltage Protection (Lower-arm, UVD)

- b1. Control supply voltage rises: After the voltage level reaches UVDr, the circuits start to operate when next input is applied.
- b2. Normal operation: IGBT ON and carrying current.
- b3. Under voltage trip (UVDt).
- b4. IGBT OFF in spite of control input condition.
- b5. Fo operation starts.
- b6. Under voltage reset (UVDr).
- b7. Normal operation: IGBT ON and carrying current.





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#### [C] Under-Voltage Protection (Upper-arm, UVDB)

- c1. Control supply voltage rises: After the voltage reaches UVDBr, the circuits start to operate when next input is applied. c2. Normal operation: IGBT ON and carrying current.
- c3. Under voltage trip (UVDBt).
- c4. IGBT OFF in spite of control input condition, but there is no Fo signal output.
- c5. Under voltage reset (UVDBr).
- c6. Normal operation: IGBT ON and carrying current.

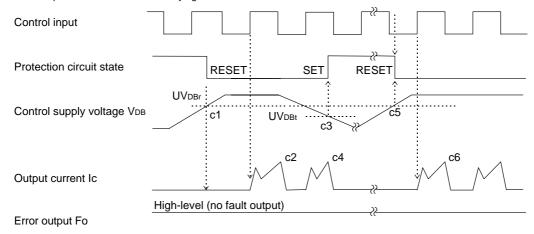
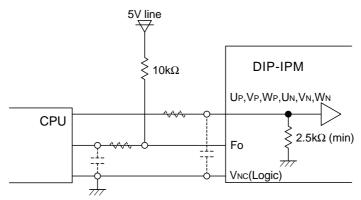
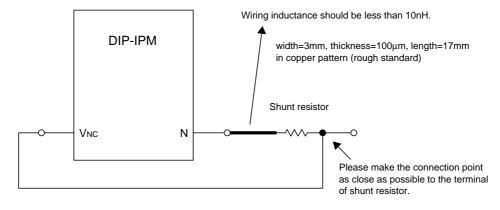


Fig. 6 RECOMMENDED CPU I/O INTERFACE CIRCUIT



Note: RC coupling at each input (parts shown dotted) may change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The DIP-IPM input signal section integrates a  $2.5k\Omega(min)$  pull-down resistor. Therefore, when using a external filtering resistor, care must be taken to satisfy the turn-on threshold voltage requirement.

Fig. 7 RECOMMENDED WIRING OF SHUNT RESISTANCE

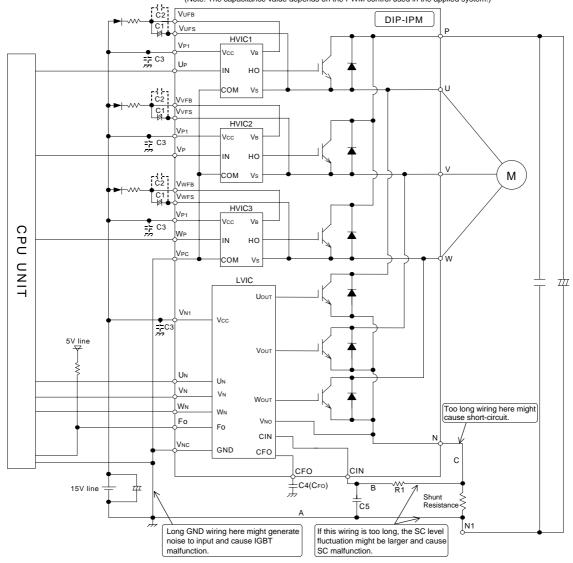




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### Fig. 8 TYPICAL DIP-IPM APPLICATION CIRCUIT EXAMPLE

C1:Tight tolerance temp-compensated electrolytic type C2,C3: 0.22~2µF R-category ceramic capacitor for noise filtering. (Note: The capacitance value depends on the PWM control used in the applied system.)



- Note 1: To prevent the input signals oscillation, the wiring of each input should be as short as possible. (2cm~3cm or less)
  - 2: By virtue of integrating an application specific type HVIC inside the module, direct coupling to CPU terminals without any opto-coupler or transformer isolation is possible.
  - 3: Fo output is open collector type. This signal line should be pulled up to the positive side of the 5V power supply with approximately 10kΩ resistor.
  - 4: Fo output pulse width is determined by the external capacitor between CFO and Vnc terminals (CFO). (Example : CFO = 22 nF → tFO = 1.8 ms (typ.))
  - 5: The logic of input signal is high-active. The DIP-IPM input signal section integrates a 2.5kΩ (min) pull-down resistor. Therefore, when using external filtering resistor, care must be taken to satisfy the turn-on threshold voltage requirement.
  - **6:** To prevent malfunction of protection, The wiring of A, B, C should be as short as possible.
  - 7: Please set the R<sub>1</sub>C<sub>5</sub> time constant in the range  $1.5\sim2\mu s$ .
  - 8: Each capacitor should be located as nearby the pins of the DIP-IPM as possible.
  - 9: To prevent surge destruction, the wiring between the smoothing capacitor and the P&N1 pins should be as short as possible. Approximately a 0.1~0.22μF snubber capacitor between the P&N1 pins is recommended.

